

EasyPACK™ module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{nom}} = 100\text{ A} / I_{CRM} = 200\text{ A}$
 - Low $V_{CE,\text{sat}}$
 - Overload operation up to 175°C
 - TRENCHSTOP™ IGBT7
- Mechanical features
 - Solder contact technology
 - High power density
 - Compact design
 - 2.5 kV AC 1 minute insulation
 - Al_2O_3 substrate with low thermal resistance



Typical appearance

Potential applications

- Air conditioning
- Auxiliary inverters
- Motor drives
- Servo drives
- UPS systems

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

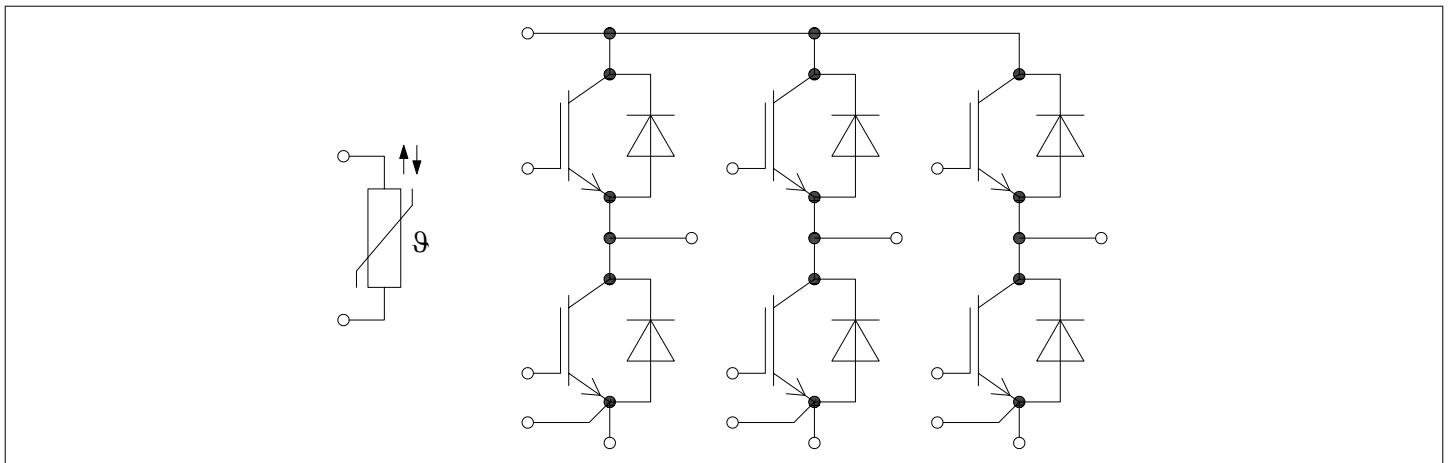


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	11.5	mm
Creepage distance	d_{Creep}	terminal to terminal	6.3	mm
Clearance	d_{Clear}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to terminal	5.0	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25 \text{ °C}$, per switch		4		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		40		80	N
Weight	G			39		g

Note: The current under continuous operation is limited to 30 A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25 \text{ °C}$	1200	V
Implemented collector current	I_{CN}		100	A
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ °C}$ $T_H = 65 \text{ °C}$	80	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$	200	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 100\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.50	1.80	V
			$T_{vj} = 125\ ^\circ C$	1.64		
			$T_{vj} = 175\ ^\circ C$	1.72		
Gate threshold voltage	V_{GETh}	$I_C = 2.5\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 600\ V$		1.8		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		1.5		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		21.7		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.075		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		0.009	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.8\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.150		μs
			$T_{vj} = 125\ ^\circ C$	0.166		
			$T_{vj} = 175\ ^\circ C$	0.174		
Rise time (inductive load)	t_r	$I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.8\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.041		μs
			$T_{vj} = 125\ ^\circ C$	0.045		
			$T_{vj} = 175\ ^\circ C$	0.047		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.8\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.300		μs
			$T_{vj} = 125\ ^\circ C$	0.380		
			$T_{vj} = 175\ ^\circ C$	0.420		
Fall time (inductive load)	t_f	$I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.8\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.100		μs
			$T_{vj} = 125\ ^\circ C$	0.180		
			$T_{vj} = 175\ ^\circ C$	0.250		
Turn-on energy loss per pulse	E_{on}	$I_C = 100\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 1.8\ \Omega, di/dt = 1700\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	6		mJ
			$T_{vj} = 125\ ^\circ C$	8.4		
			$T_{vj} = 175\ ^\circ C$	10.1		
Turn-off energy loss per pulse	E_{off}	$I_C = 100\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 1.8\ \Omega, dv/dt = 2850\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	6		mJ
			$T_{vj} = 125\ ^\circ C$	9.6		
			$T_{vj} = 175\ ^\circ C$	12		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$		370	A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$		350	
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.700		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note: $T_{vj op} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V	
Continuous DC forward current	I_F		100	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	200	A	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	970	A^2s
			$T_{vj} = 175 \text{ }^\circ\text{C}$	860	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 100 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.72	2.10	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.59		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.52		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 100 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1700 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		60		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		79		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		91		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 600\text{ V}, I_F = 100\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1700\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$		7.1	μC
			$T_{vj} = 125\text{ }^\circ\text{C}$		12.7	
			$T_{vj} = 175\text{ }^\circ\text{C}$		17.3	
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}, I_F = 100\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1700\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$		2.4	mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$		3.9	
			$T_{vj} = 175\text{ }^\circ\text{C}$		5.6	
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		0.966		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$

Note: $T_{vj\text{ op}} > 150\text{ }^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ }^\circ\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ }^\circ\text{C}, R_{100} = 493\text{ }\Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ }^\circ\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

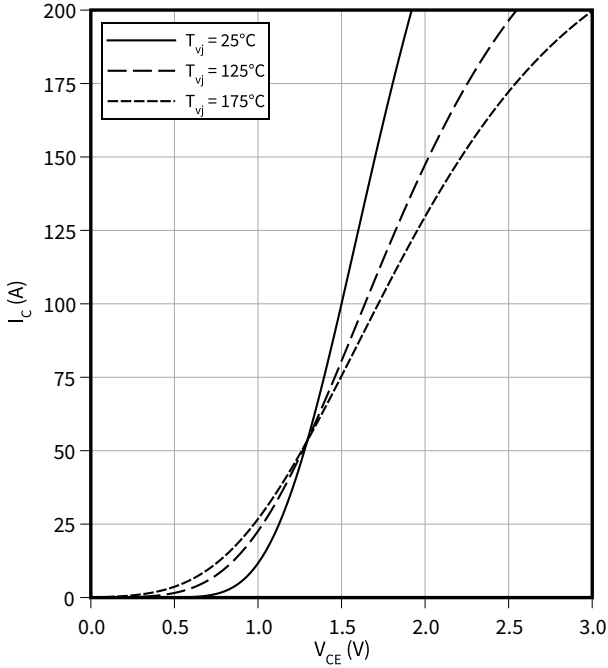
Note: Specification according to the valid application note.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

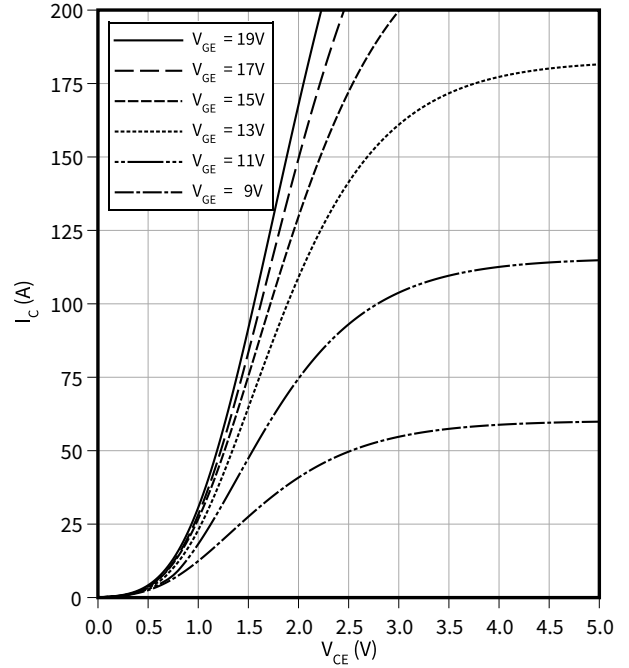
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

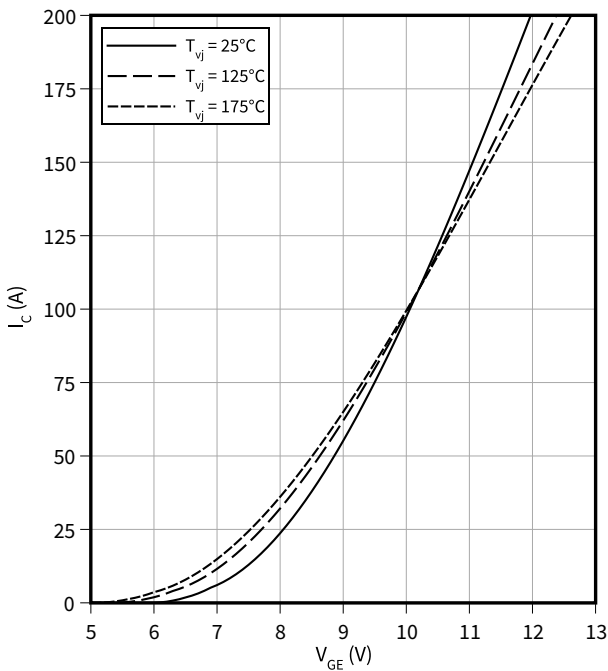
$$T_{vj} = 175 \text{ °C}$$



Transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

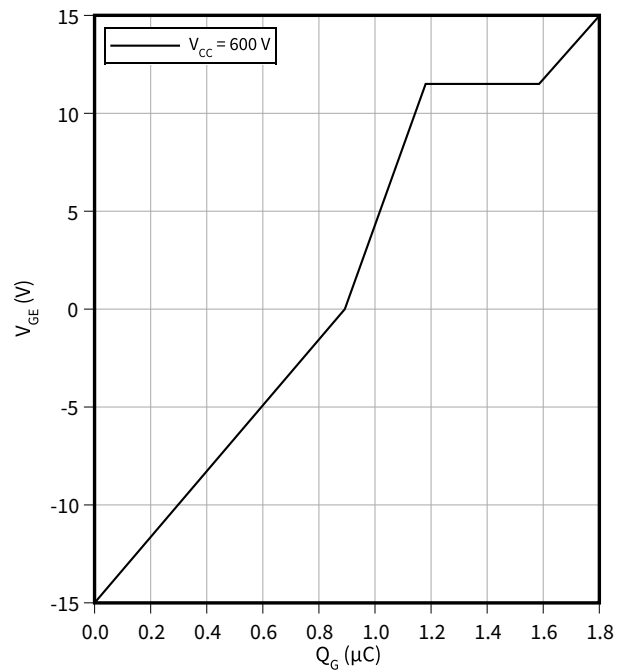
$$V_{CE} = 20 \text{ V}$$



Gate charge characteristic (typical), IGBT, Inverter

$$V_{GE} = f(Q_G)$$

$$I_C = 100 \text{ A}, T_{vj} = 25 \text{ °C}$$

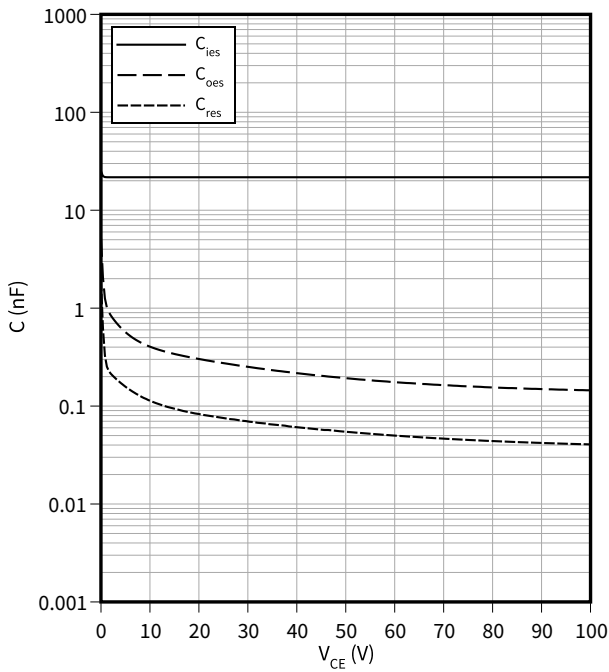


5 Characteristics diagrams

Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

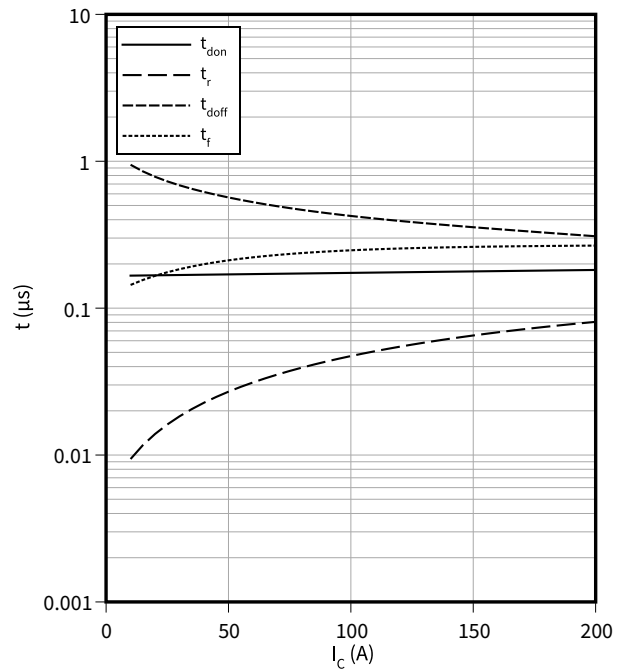
$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

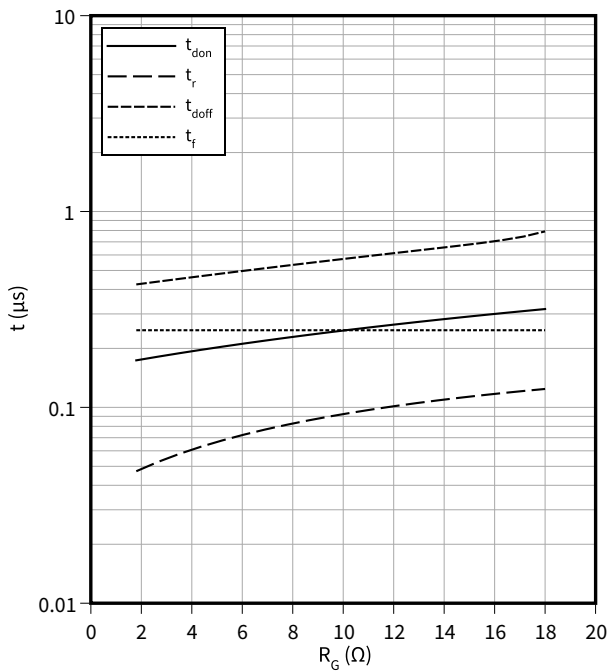
$R_{Goff} = 1.8 \text{ } \Omega, R_{Gon} = 1.8 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, Inverter

$t = f(R_G)$

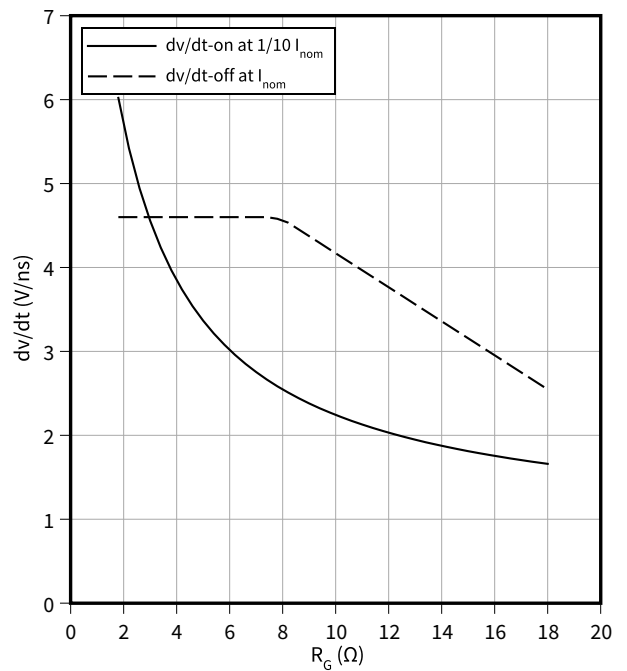
$V_{GE} = \pm 15 \text{ V}, I_C = 100 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$

$I_C = 100 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$

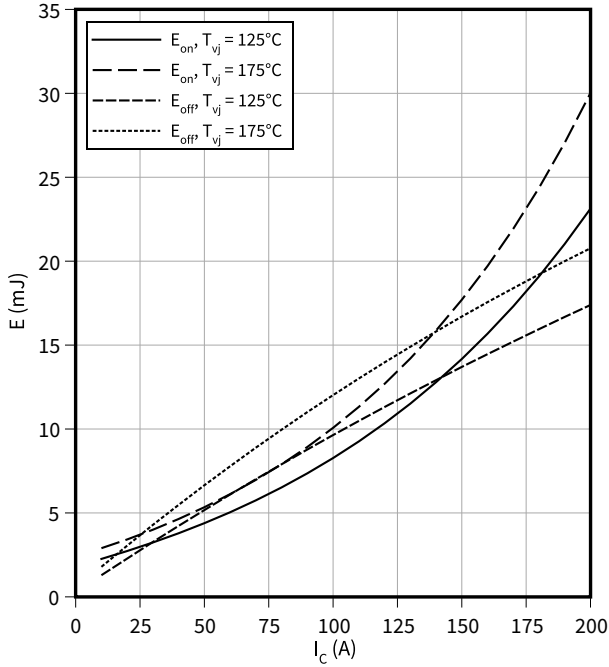


5 Characteristics diagrams

Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

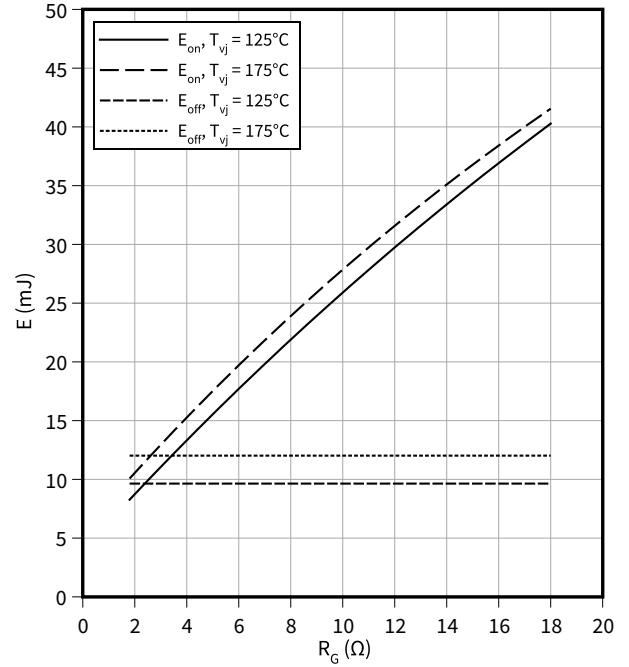
$R_{Goff} = 1.8 \Omega$, $R_{Gon} = 1.8 \Omega$, $V_{GE} = \pm 15 V$, $V_{CC} = 600 V$



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

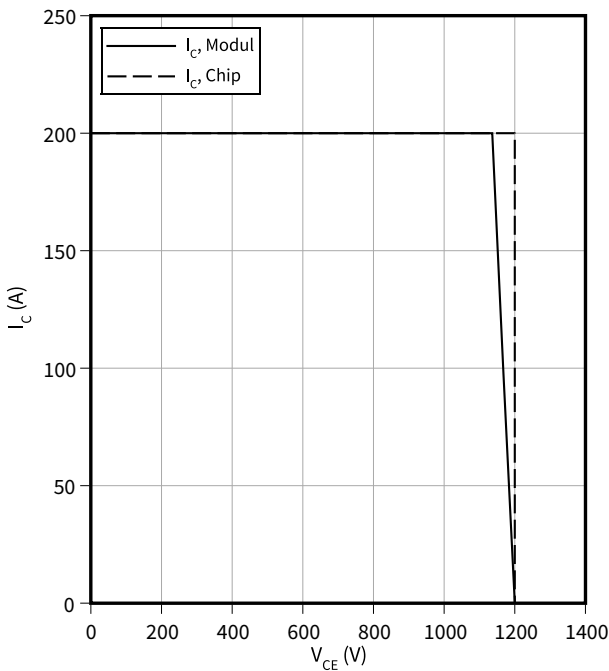
$V_{GE} = \pm 15 V$, $I_C = 100 A$, $V_{CC} = 600 V$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

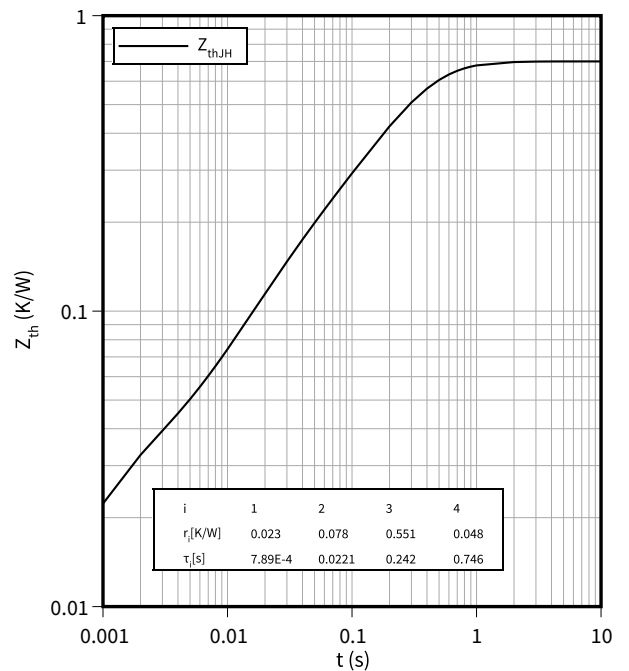
$I_C = f(V_{CE})$

$R_{Goff} = 1.8 \Omega$, $V_{GE} = \pm 15 V$, $T_{vj} = 175 \text{ °C}$



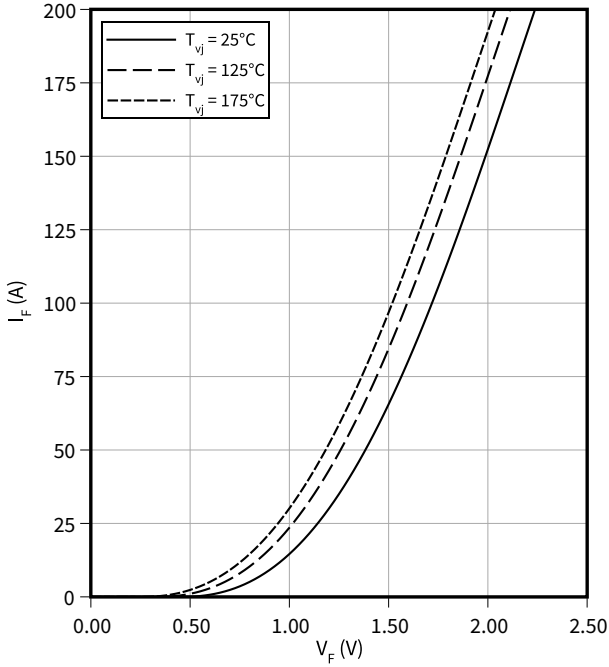
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

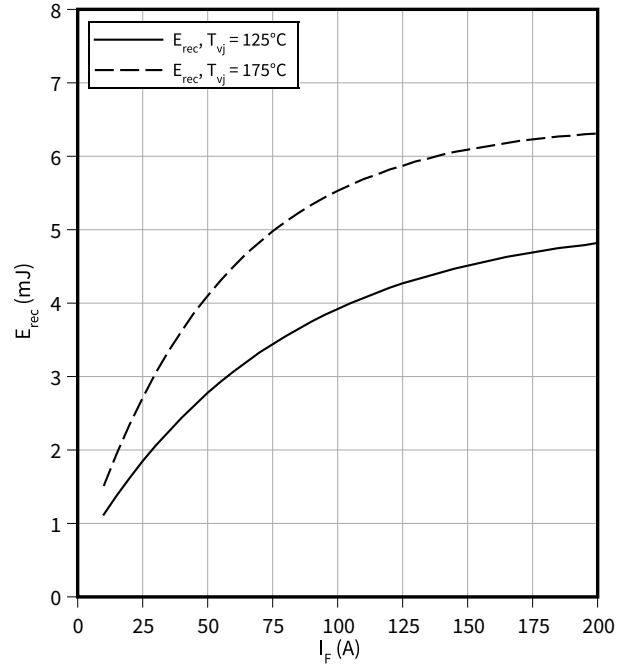
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

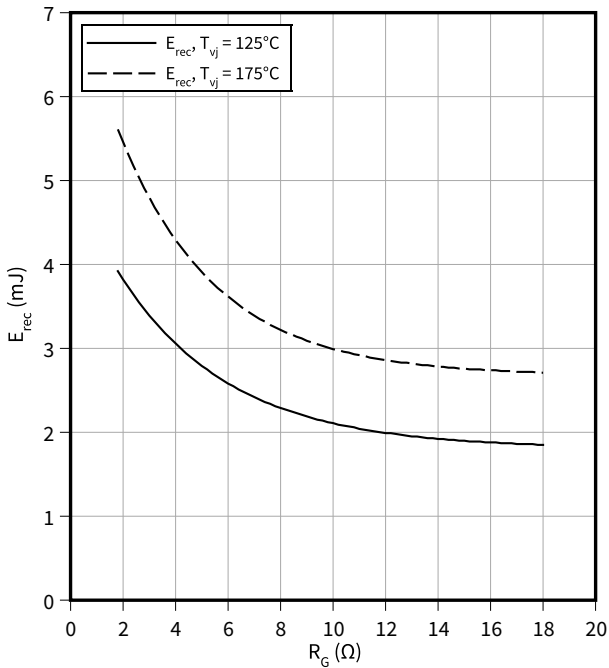
$R_{Gon} = 1.8 \Omega, V_{CC} = 600 \text{ V}$



Switching losses (typical), Diode, Inverter

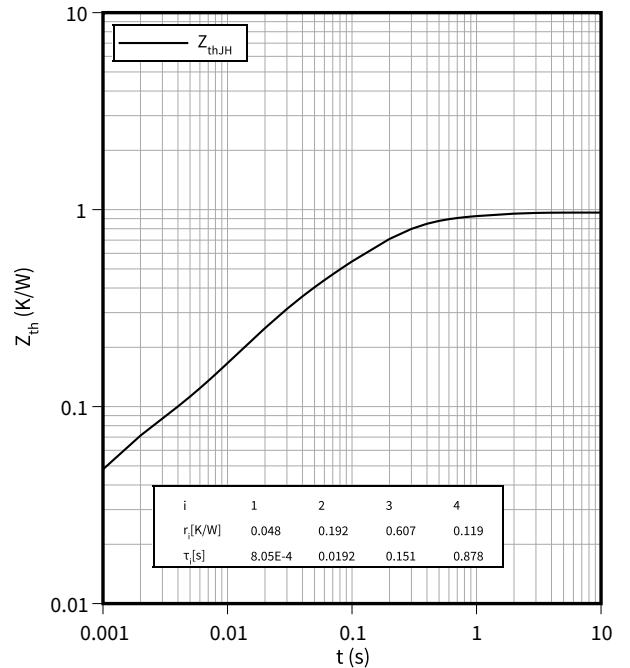
$E_{rec} = f(R_G)$

$I_F = 100 \text{ A}, V_{CC} = 600 \text{ V}$



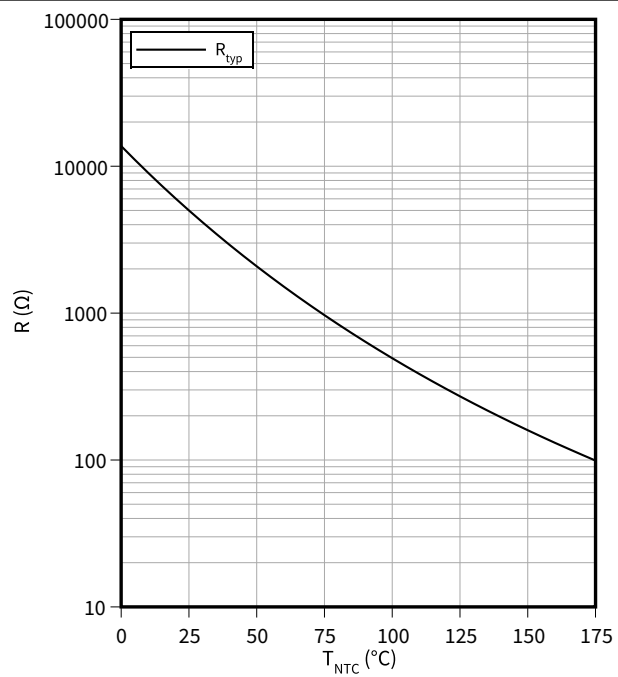
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



6 Circuit diagram

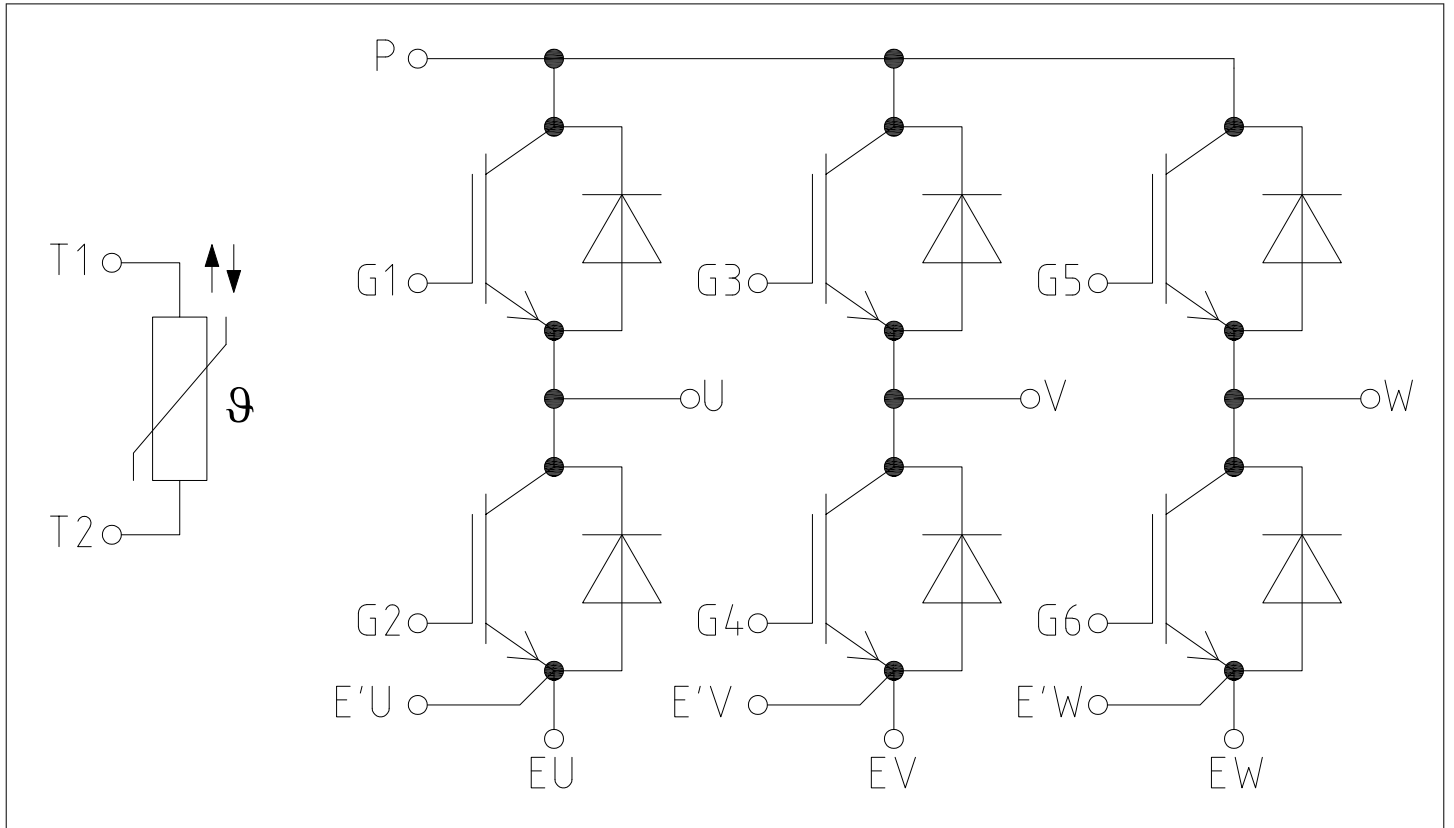


Figure 1

8 Module label code

Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	Content	Digit	Example
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example			
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
V2.0	2019-08-12	Preliminary datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2023-05-19	Final datasheet

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